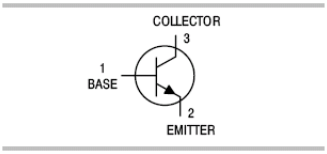
BC817-16/-25/-40

SOT-23 Bipolar Transistor(NPN)

Features

- Epitaxial planar die construction
- Complimentary to BC807
- High collector current
- High current gain
- Low collector-emitter saturation voltage



Mechanic al Data

- Case: SOT-23
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

SOT-23

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BC817-16	SOT-23	3000 pcs / Tape & Reel	6A
BC817-25	SOT-23	3000 pcs / Tape & Reel	6B▪
BC817-40	SOT-23	3000 pcs / Tape & Reel	6C

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V_{CBO}	50	V
Collector-Emitter Breakdown Voltage	V_{CEO}	45	V
Emitter-Base Breakdown Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	0.5	A
Peak Collector Current	I_{CM}	1	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	300	mW
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	398	°C/W
Thermal Resistance Junction-to-Case *1	$R_{\theta JC}$	230	°C/W
Thermal Resistance Junction-to-Lead *1	$R_{\theta JL}$	202	°C/W
Operating junction Temperature	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a 15mm * 15mm * 1mm FR4-epoxy P.C.B

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C = 100μA, I_E = 0	50	-	-	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	45	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E = 100μA, I_C = 0	5	-	-	V
Collector Cut-off Current		I_{CBO}	V_{CB} = 25V, I_E = 0	-	-	100	nA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 4V, I_C = 0	-	-	100	nA
DC Current Gain	BC817-16	h_{FE}		100	213	250	-
	BC817-25			160	333	400	-
	BC817-40			250	383	600	-
	BC817-16		V_{CE} = 1V, I_C = 300mA	60	-	-	-
	BC817-25			100	-	-	-
	BC817-40			170	-	-	-
	BC817-40		V_{CE} = 1V, I_C = 500mA	40	-	-	-
Collector-emitter Saturation Voltage		$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	-	-	0.7	V
Base-emitter Saturation Voltage		$V_{BE(sat)}$	I_C = 500mA, I_B = 50mA	-	-	1.2	V
Transition Frequency		f_T	I_C = 50mA, V_{CE} = 5V	-	170	-	MHz
Collector Output Capacitance		C_{OBO}	V_{CB} = 10V, I_E = 0, f = 1MHZ	-	6	-	pF

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

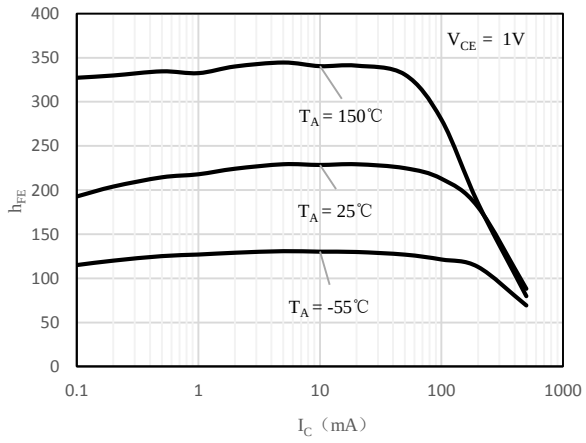


Fig 1 h_{FE} vs. I_C (BC817-16)

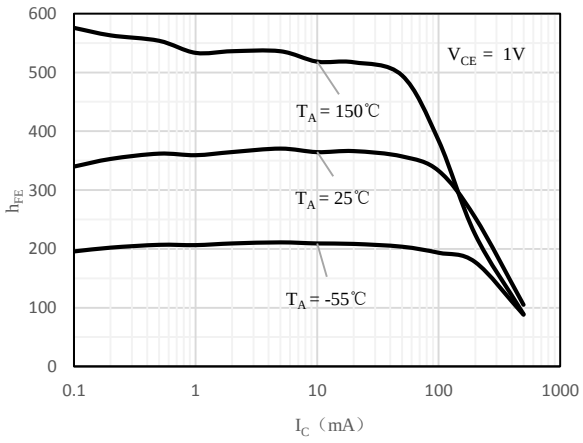


Fig 2 h_{FE} vs. I_C (BC817-25)

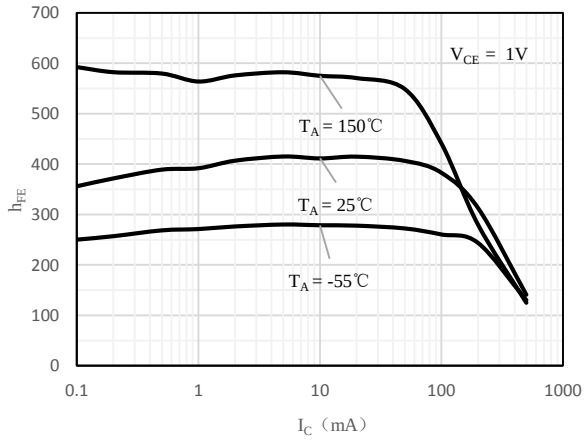


Fig 3 h_{FE} vs. I_C (BC817-40)

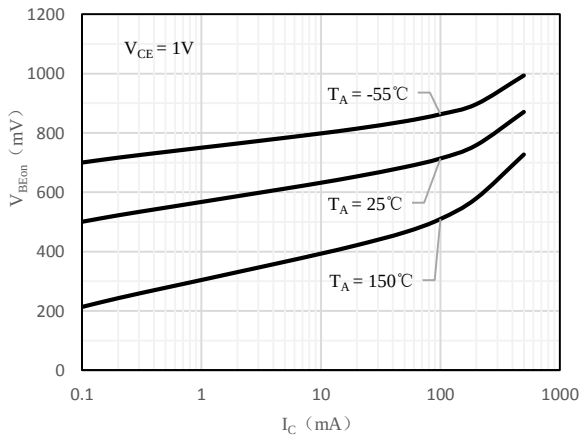


Fig 4 $V_{BE(ON)}$ vs. I_C

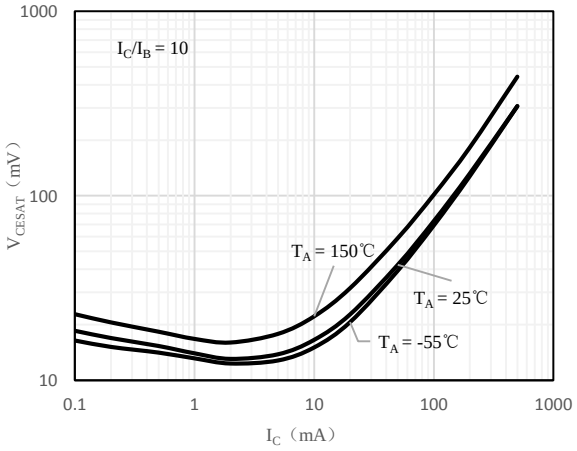


Fig 2 $V_{CE(sat)}$ vs. I_C

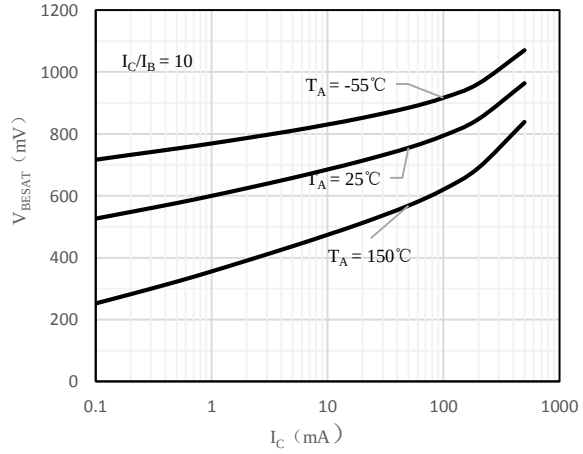


Fig 3 $V_{BE(sat)}$ vs. I_C

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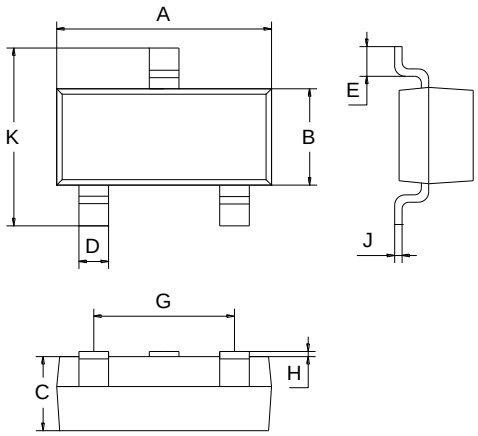
SOT-23 Bipolar Transistor(NPN)

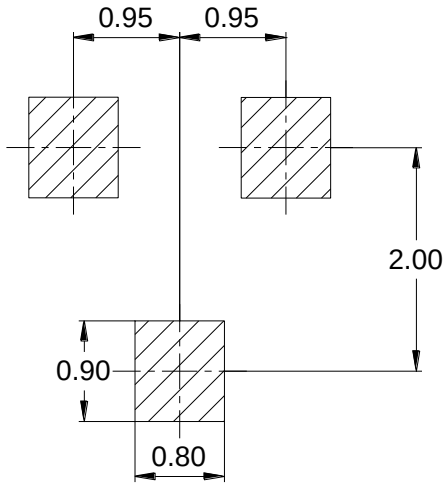
Package Outline Dimensions (Unit: mm)



SOT-23		
Dimension	**Min.**	**Max.**
A	2.70	3.10
B	1.10	1.50
C	0.9	1.1
D	0.3	0.5
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.05	0.15
K	2.20	2.60

Package Outline Dimensions (Unit: mm)

SOT-23



Package	Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
SOT-23	3000pcs	7inch	45,000pcs	203×203×195	180,000pcs	438×438×220